

**AMENDMENTS TO THE CLAIMS:**

1. (Amended) A semiconductor apparatus, comprising:

a substrate having a transistor formed thereon;

a ~~first electrode formed on~~ plurality of first capacitor electrodes secured to said  
substrate and ~~connected to said transistor~~;

a ~~second electrode formed on~~ plurality of second electrodes secured to said substrate  
and electrically separated from said first electrodes; and

an insulating film formed ~~on said substrate~~ so as to cover said first ~~electrode~~  
electrodes and which is between the first electrodes and second electrodes,

wherein the first and second electrodes have a common bottom level and the plurality  
of second electrodes each have a top surface which is above a top surface of the first  
electrodes.

~~wherein, when a plane of said insulating film which is not on a side of said substrate~~  
~~is taken as a first plane, a surface facing said first plane of said first electrode is taken as a~~  
~~first surface, and a surface facing said first plane of said second electrode is taken as a second~~  
~~surface, a distance between a surface of said substrate and said second surface is larger than a~~  
~~distance between the surface of said substrate and said first surface.~~

2. (Amended) The semiconductor apparatus according to claim 1, wherein said ~~second surface~~ top surface of the second electrodes is substantially equivalent to a top surface of said insulating film.

3. (Amended) The semiconductor apparatus according to claim 1, wherein ~~the~~ a distance between ~~the~~ a top surface of said substrate and said ~~second surface~~ top surface of the second electrodes is larger than a distance between the top surface of said substrate and the top surface of said insulating film.

4. (Amended) The semiconductor apparatus according to claim 1, wherein said second electrodes are ~~is~~ fixed ~~in~~ to a constant potential.

5. (Amended) The semiconductor apparatus according to claim 1, wherein a plurality of said first electrodes are arranged in a matrix form, and said second ~~electrode is~~ electrodes are disposed between said plurality of first electrodes.

6. (Amended) The semiconductor apparatus according to claim 5, wherein ~~a~~ said plurality of ~~said~~ second electrodes are arranged in a matrix form.

7. (Amended) The semiconductor apparatus according to claim 1, wherein at least one of said first ~~electrode is~~ electrodes are connected to a first terminal of said transistor, and a

second terminal of said transistor is connected to a bit line and a capacitance element to which a potential is applied.

8. (Amended) The semiconductor apparatus according to claim 2, wherein said second ~~electrode is~~ electrodes are fixed ~~in~~ to a constant potential.

9. (Amended) The semiconductor apparatus according to claim 3, wherein said second ~~electrode is~~ electrodes are fixed ~~in~~ to a constant potential.

10. (Amended) The semiconductor apparatus according to claim 1, wherein said second ~~electrode is~~ electrodes are electrically connected to a corresponding pad electrode which is connected to a lead for taking a signal out.

11. (Amended) A semiconductor apparatus for recognizing a fingerprint, comprising:  
~~a semiconductor substrate having a transistor;~~  
~~a first electrode formed on said~~ plurality of first capacitor electrodes secured to a  
semiconductor substrate ~~and connected to said transistor;~~  
~~a second electrode formed on~~ plurality of second electrodes secured to said  
semiconductor substrate and electrically separated from said first ~~electrode~~ electrodes; and  
an insulating film formed on said semiconductor substrate so as to cover said ~~first~~  
~~electrode~~ plurality of first electrodes,

wherein the first and second electrodes have a common bottom level and the plurality of second electrodes each have a top surface which is above a top surface of the first electrodes.

~~wherein, when a plane of said insulating film on which said fingerprint is placed is taken as a first plane, a surface facing said first plane of said first electrode is taken as a first surface, and a surface facing said first plane of said second electrode is taken as a second surface, a distance between a surface of said semiconductor substrate and said second surface is larger than a distance between the surface of said semiconductor substrate and said first surface.~~

12. (Amended) The semiconductor apparatus according to claim 11, wherein said ~~second surface~~ top surface of said second electrodes is substantially equivalent to a top surface of said insulating film.

13. (Amended) The semiconductor apparatus according to claim 11, wherein ~~the~~ a distance between ~~the~~ a top surface of said semiconductor substrate and said ~~second surface~~ top surface of said second electrodes is larger than a distance between the top surface of said semiconductor substrate and the top surface of said insulating film.

14. (Amended) The semiconductor apparatus according to claim 11, wherein said second ~~electrodes are electrode~~ is fixed in to a constant potential.

15. (Amended) The semiconductor apparatus according to claim 11, wherein a plurality of said first electrodes are arranged in a matrix form, and said second ~~electrode is~~ electrodes are disposed between said plurality of first electrodes.

16. (Amended) The semiconductor apparatus according to claim 15, wherein ~~a~~ said plurality of ~~said~~ second electrodes are arranged in a matrix form.

17. (Amended) The semiconductor apparatus according to claim 11, wherein at least one of said first electrodes are ~~electrode is~~ connected to a first terminal of ~~said~~ a transistor formed on said substrate, and a second terminal of said transistor is connected to a bit line and a capacitance element to which a potential is applied.

18. (Amended) The semiconductor apparatus according to claim 12, wherein said second electrodes ~~is~~ are fixed ~~in~~ to a constant potential.

19. (Amended) The semiconductor apparatus according to claim 13, wherein said second electrodes ~~is~~ are fixed ~~in~~ to a constant potential.

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20. (Amended) The semiconductor apparatus according to claim 11, wherein said second electrodes is are respectively electrically connected to a corresponding pad electrode which is connected to a lead for taking a signal out.